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Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	234720
Number of Logic Elements/Cells	622000
Total RAM Bits	51200000
Number of I/O	600
Number of Gates	-
Voltage - Supply	0.87V ~ 0.93V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1517-BBGA, FCBGA
Supplier Device Package	1517-FBGA (40x40)
Purchase URL	https://www.e-xfl.com/product-detail/intel/5sgxma7n1f40c1n

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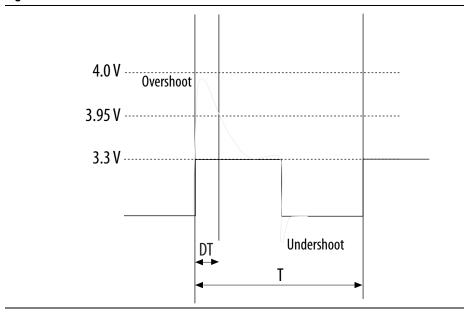
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Table 5 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage of device lifetime. The maximum allowed overshoot duration is specified as a percentage of high time over the lifetime of the device. A DC signal is equivalent to 100% of the duty cycle. For example, a signal that overshoots to 3.95 V can be at 3.95 V for only ~21% over the lifetime of the device; for a device lifetime of 10 years, the overshoot duration amounts to ~2 years.

Table 5. Maximum Allowed Overshoot During Transitions

Symbol	Description	Condition (V)	Overshoot Duration as % @ T _J = 100°C	Unit
		3.8	100	%
		3.85	64	%
		3.9	36	%
		3.95	21	%
Vi (AC)	AC input voltage	4	12	%
		4.05	7	%
		4.1	4	%
		4.15	2	%
		4.2	1	%

Figure 1. Stratix V Device Overshoot Duration



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I/O Pin Leakage Current

Table 9 lists the Stratix V I/O pin leakage current specifications.

Table 9. I/O Pin Leakage Current for Stratix V Devices (1)

Symbol	Description	Description Conditions		Тур	Max	Unit
I _I	Input pin	$V_I = 0 V to V_{CCIOMAX}$	-30	_	30	μA
I _{OZ}	Tri-stated I/O pin	$V_0 = 0 V \text{ to } V_{\text{CCIOMAX}}$	-30		30	μΑ

Note to Table 9:

(1) If $V_0 = V_{CCIO}$ to $V_{CCIOMax}$, 100 μA of leakage current per I/O is expected.

Bus Hold Specifications

Table 10 lists the Stratix V device family bus hold specifications.

Table 10. Bus Hold Parameters for Stratix V Devices

							V	CIO					
Parameter	Symbol	mbol Conditions	1.2	1.2 V		1.5 V		B V	2.5 V		3.0 V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Low sustaining current	I _{SUSL}	V _{IN} > V _{IL} (maximum)	22.5	_	25.0	_	30.0	_	50.0	_	70.0	_	μА
High sustaining current	I _{SUSH}	V _{IN} < V _{IH} (minimum)	-22.5	_	-25.0	_	-30.0	_	-50.0		-70.0		μА
Low overdrive current	I _{ODL}	0V < V _{IN} < V _{CCIO}	_	120	_	160	_	200	_	300	_	500	μА
High overdrive current	I _{ODH}	0V < V _{IN} < V _{CCIO}	_	-120	_	-160	_	-200	_	-300	_	-500	μА
Bus-hold trip point	V_{TRIP}	_	0.45	0.95	0.50	1.00	0.68	1.07	0.70	1.70	0.80	2.00	V

On-Chip Termination (OCT) Specifications

If you enable OCT calibration, calibration is automatically performed at power-up for I/Os connected to the calibration block. Table 11 lists the Stratix V OCT termination calibration accuracy specifications.

Table 11. OCT Calibration Accuracy Specifications for Stratix V Devices (1) (Part 1 of 2)

Symbol			Calibration Accuracy				
	Description	Conditions	C 1	C2,I2	C3,I3, I3YY	C4,I4	Unit
25-Ω R _S	Internal series termination with calibration (25- Ω setting)	V _{CCIO} = 3.0, 2.5, 1.8, 1.5, 1.2 V	±15	±15	±15	±15	%

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Symbol			Resistance Tolerance					
	Description	Conditions	C1	C2,I2	C3, I3, I3YY	C4, I4	Unit	
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	V _{CCIO} = 1.8 and 1.5 V	±30	±30	±40	±40	%	
50-Ω R _S	Internal series termination without calibration (50- Ω setting)	V _{CCIO} = 1.2 V	±35	±35	±50	±50	%	
100-Ω R _D	Internal differential termination (100-Ω setting)	V _{CCPD} = 2.5 V	±25	±25	±25	±25	%	

Calibration accuracy for the calibrated series and parallel OCTs are applicable at the moment of calibration. When voltage and temperature conditions change after calibration, the tolerance may change.

OCT calibration is automatically performed at power-up for OCT-enabled I/Os. Table 13 lists the OCT variation with temperature and voltage after power-up calibration. Use Table 13 to determine the OCT variation after power-up calibration and Equation 1 to determine the OCT variation without recalibration.

Equation 1. OCT Variation Without Recalibration for Stratix V Devices (1), (2), (3), (4), (5), (6)

$$R_{OCT} = R_{SCAL} \Big(1 + \langle \frac{dR}{dT} \times \Delta T \rangle \pm \langle \frac{dR}{dV} \times \Delta V \rangle \Big)$$

Notes to Equation 1:

- (1) The R_{OCT} value shows the range of OCT resistance with the variation of temperature and V_{CCIO} .
- (2) R_{SCAL} is the OCT resistance value at power-up.
- (3) ΔT is the variation of temperature with respect to the temperature at power-up.
- (4) ΔV is the variation of voltage with respect to the V_{CCIO} at power-up.
- (5) dR/dT is the percentage change of R_{SCAL} with temperature.
- (6) dR/dV is the percentage change of R_{SCAL} with voltage.

Table 13 lists the on-chip termination variation after power-up calibration.

Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 1 of 2) (1)

Symbol	Description	V _{CCIO} (V)	Typical	Unit
		3.0	0.0297	
	OCT variation with voltage without recalibration	2.5	0.0344	
dR/dV		1.8	0.0499	%/mV
		1.5	0.0744	
		1.2	0.1241	

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Table 13. OCT Variation after Power-Up Calibration for Stratix V Devices (Part 2 of 2) (1)

Symbol	Description	V _{CCIO} (V)	Typical	Unit
		3.0	0.189	
	OCT variation with temperature without recalibration	2.5	0.208	
dR/dT		1.8	0.266	%/°C
		1.5	0.273	1
		1.2	0.317	

Note to Table 13:

(1) Valid for a V_{CCIO} range of $\pm 5\%$ and a temperature range of 0° to $85^\circ\text{C}.$

Pin Capacitance

Table 14 lists the Stratix V device family pin capacitance.

Table 14. Pin Capacitance for Stratix V Devices

Symbol	ymbol Description				
C _{IOTB}	Input capacitance on the top and bottom I/O pins	6	pF		
C _{IOLR}	Input capacitance on the left and right I/O pins	6	pF		
C _{OUTFB}	Input capacitance on dual-purpose clock output and feedback pins	6	pF		

Hot Socketing

Table 15 lists the hot socketing specifications for Stratix V devices.

Table 15. Hot Socketing Specifications for Stratix V Devices

Symbol	Description	Maximum
I _{IOPIN (DC)}	DC current per I/O pin	300 μΑ
I _{IOPIN (AC)}	AC current per I/O pin	8 mA ⁽¹⁾
I _{XCVR-TX (DC)}	DC current per transceiver transmitter pin	100 mA
I _{XCVR-RX (DC)}	DC current per transceiver receiver pin	50 mA

Note to Table 15:

(1) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|I_{IOPIN}| = C dv/dt$, in which C is the I/O pin capacitance and dv/dt is the slew rate.

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Table 18. Single-Ended SSTL, HSTL, and HSUL I/O Reference Voltage Specifications for Stratix V Devices

I/O Standard		V _{CCIO} (V)		V _{REF} (V)			V _{TT} (V)			
I/O Standard	Min	Тур	Max	Min	Тур	Max	Min	Тур	Мах	
SSTL-2 Class I, II	2.375	2.5	2.625	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	V _{REF} – 0.04	V_{REF}	V _{REF} + 0.04	
SSTL-18 Class I, II	1.71	1.8	1.89	0.833	0.9	0.969	V _{REF} – 0.04	V _{REF}	V _{REF} + 0.04	
SSTL-15 Class I, II	1.425	1.5	1.575	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}	
SSTL-135 Class I, II	1.283	1.35	1.418	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	
SSTL-125 Class I, II	1.19	1.25	1.26	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}	
SSTL-12 Class I, II	1.14	1.20	1.26	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	0.49 * V _{CCIO}	0.5 * VCCIO	0.51 * V _{CCIO}	
HSTL-18 Class I, II	1.71	1.8	1.89	0.85	0.9	0.95	_	V _{CCIO} /2	_	
HSTL-15 Class I, II	1.425	1.5	1.575	0.68	0.75	0.9	_	V _{CCIO} /2	_	
HSTL-12 Class I, II	1.14	1.2	1.26	0.47 * V _{CCIO}	0.5 * V _{CCIO}	0.53 * V _{CCIO}	_	V _{CCIO} /2	_	
HSUL-12	1.14	1.2	1.3	0.49 * V _{CCIO}	0.5 * V _{CCIO}	0.51 * V _{CCIO}	_	_	_	

Table 19. Single-Ended SSTL, HSTL, and HSUL I/O Standards Signal Specifications for Stratix V Devices (Part 1 of 2)

I/O Standard	V _{IL(D(}	_{C)} (V)	V _{IH(D}	_{C)} (V)	V _{IL(AC)} (V)	V _{IH(AC)} (V)	V _{OL} (V)	V _{OH} (V)	I (mA)	l _{oh}
i/U Stanuaru	Min	Max	Min	Max	Max	Min	Max	Min	I _{ol} (mA)	(mA)
SSTL-2 Class I	-0.3	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.3	V _{REF} – 0.31	V _{REF} + 0.31	V _{TT} – 0.608	V _{TT} + 0.608	8.1	-8.1
SSTL-2 Class II	-0.3	V _{REF} – 0.15	V _{REF} + 0.15	V _{CCIO} + 0.3	V _{REF} – 0.31	V _{REF} + 0.31	V _{TT} – 0.81	V _{TT} + 0.81	16.2	-16.2
SSTL-18 Class I	-0.3	V _{REF} – 0.125	V _{REF} + 0.125	V _{CCIO} + 0.3	V _{REF} – 0.25	V _{REF} + 0.25	V _{TT} – 0.603	V _{TT} + 0.603	6.7	-6.7
SSTL-18 Class II	-0.3	V _{REF} – 0.125	V _{REF} + 0.125	V _{CCIO} + 0.3	V _{REF} – 0.25	V _{REF} + 0.25	0.28	V _{CCIO} - 0.28	13.4	-13.4
SSTL-15 Class I	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.175	V _{REF} + 0.175	0.2 * V _{CCIO}	0.8 * V _{CCIO}	8	-8
SSTL-15 Class II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.175	V _{REF} + 0.175	0.2 * V _{CCIO}	0.8 * V _{CCIO}	16	-16
SSTL-135 Class I, II	_	V _{REF} – 0.09	V _{REF} + 0.09	_	V _{REF} – 0.16	V _{REF} + 0.16	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_
SSTL-125 Class I, II	_	V _{REF} – 0.85	V _{REF} + 0.85	_	V _{REF} – 0.15	V _{REF} + 0.15	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_
SSTL-12 Class I, II	_	V _{REF} – 0.1	V _{REF} + 0.1	_	V _{REF} – 0.15	V _{REF} + 0.15	0.2 * V _{CCIO}	0.8 * V _{CCIO}	_	_

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Table 23. Transceiver Specifications for Stratix V GX and GS Devices (1) (Part 6 of 7)

Symbol/	Conditions	Trai	nsceive Grade	r Speed e 1	Trar	sceive Grade	r Speed 2	Tran	sceive Grade	er Speed e 3	Unit
Description		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Inter-transceiver block transmitter channel-to- channel skew	xN PMA bonded mode	ı	ı	500	_	ı	500	_	_	500	ps
CMU PLL											
Supported Data Range	_	600	_	12500	600	_	12500	600	_	8500/ 10312.5 (24)	Mbps
t _{pll_powerdown} (15)	_	1	_	_	1	_	_	1	_	_	μs
t _{pll_lock} (16)	_	_	_	10	_	_	10	_	_	10	μs
ATX PLL											
	VCO post-divider L=2	8000		14100	8000		12500	8000	_	8500/ 10312.5 (24)	Mbps
Currented Date	L=4	4000	_	7050	4000	_	6600	4000	_	6600	Mbps
Supported Data Rate Range	L=8	2000	_	3525	2000	_	3300	2000	_	3300	Mbps
S	L=8, Local/Central Clock Divider =2	1000	_	1762.5	1000	_	1762.5	1000	_	1762.5	Mbps
t _{pll_powerdown} (15)	_	1	_	_	1	_	_	1	_	_	μs
t _{pll_lock} (16)	_		_	10	_	_	10	_	_	10	μs
fPLL											
Supported Data Range	_	600	_	3250/ 3125 ⁽²⁵⁾	600	_	3250/ 3125 ⁽²⁵⁾	600	_	3250/ 3125 ⁽²⁵⁾	Mbps
t _{pll_powerdown} (15)	_	1	_		1	_		1			μs

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Table 23. Transceiver Specifications for Stratix V GX and GS Devices (1) (Part 7 of 7)

Symbol/ Description	Conditions	Transceiver Speed Grade 1			Trar	sceive Grade	r Speed 2	Tran	Unit		
Description		Min	Min Typ Max		Min	Тур	Max	Min	Тур	Max	
t _{pll_lock} (16)	_		_	10	_	_	10	_	_	10	μs

Notes to Table 23:

- (1) Speed grades shown in Table 23 refer to the PMA Speed Grade in the device ordering code. The maximum data rate could be restricted by the Core/PCS speed grade. Contact your Altera Sales Representative for the maximum data rate specifications in each speed grade combination offered. For more information about device ordering codes, refer to the *Stratix V Device Overview*.
- (2) The reference clock common mode voltage is equal to the V_{CCR_GXB} power supply level.
- (3) This supply must be connected to 1.0 V if the transceiver is configured at a data rate > 6.5 Gbps, and to 1.05 V if configured at a data rate > 10.3 Gbps when DFE is used. For data rates up to 6.5 Gbps, you can connect this supply to 0.85 V.
- (4) This supply follows VCCR_GXB.
- (5) The device cannot tolerate prolonged operation at this absolute maximum.
- (6) The differential eye opening specification at the receiver input pins assumes that **Receiver Equalization** is disabled. If you enable **Receiver Equalization**, the receiver circuitry can tolerate a lower minimum eye opening, depending on the equalization level.
- (7) The Quartus II software automatically selects the appropriate slew rate depending on the configured data rate or functional mode.
- (8) The input reference clock frequency options depend on the data rate and the device speed grade.
- (9) The line data rate may be limited by PCS-FPGA interface speed grade.
- (10) Refer to Figure 1 for the GX channel AC gain curves. The total effective AC gain is the AC gain minus the DC gain.
- (11) t_{LTR} is the time required for the receive CDR to lock to the input reference clock frequency after coming out of reset.
- (12) t_{I TD} is time required for the receiver CDR to start recovering valid data after the rx_is_lockedtodata signal goes high.
- (13) t_{LTD_manual} is the time required for the receiver CDR to start recovering valid data after the rx_is_lockedtodata signal goes high when the CDR is functioning in the manual mode.
- (14) t_{LTR_LTD_manual} is the time the receiver CDR must be kept in lock to reference (LTR) mode after the rx_is_lockedtoref signal goes high when the CDR is functioning in the manual mode.
- (15) $t_{pll\ powerdown}$ is the PLL powerdown minimum pulse width.
- (16) t_{nll lock} is the time required for the transmitter CMU/ATX PLL to lock to the input reference clock frequency after coming out of reset.
- (17) To calculate the REFCLK rms phase jitter requirement for PCle at reference clock frequencies other than 100 MHz, use the following formula: REFCLK rms phase jitter at f(MHz) = REFCLK rms phase jitter at 100 MHz × 100/f.
- (18) The maximum peak to peak differential input voltage V_{ID} after device configuration is equal to 4 × (absolute V_{MAX} for receiver pin V_{ICM}).
- (19) For ES devices, R_{REF} is 2000 Ω ±1%.
- (20) To calculate the REFCLK phase noise requirement at frequencies other than 622 MHz, use the following formula: REFCLK phase noise at f(MHz) = REFCLK phase noise at 622 MHz + 20*log(f/622).
- (21) SFP/+ optical modules require the host interface to have RD+/- differentially terminated with 100 Ω. The internal OCT feature is available after the Stratix V FPGA configuration is completed. Altera recommends that FPGA configuration is completed before inserting the optical module. Otherwise, minimize unnecessary removal and insertion with unconfigured devices.
- (22) Refer to Figure 2.
- (23) For oversampling designs to support data rates less than the minimum specification, the CDR needs to be in LTR mode only.
- (24) I3YY devices can achieve data rates up to 10.3125 Gbps.
- (25) When you use fPLL as a TXPLL of the transceiver.
- (26) REFCLK performance requires to meet transmitter REFCLK phase noise specification.
- (27) Minimum eye opening of 85 mV is only for the unstressed input eye condition.

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Table 31. PLL Specifications for Stratix V Devices (Part 2 of 3)

Symbol	Parameter	Min	Тур	Max	Unit
→ (3) (4)	Input clock cycle-to-cycle jitter (f _{REF} ≥ 100 MHz)	_	_	0.15	UI (p-p)
t _{INCCJ} (3), (4)	Input clock cycle-to-cycle jitter (f _{REF} < 100 MHz)	-750		+750	ps (p-p)
+ (5)	Period Jitter for dedicated clock output ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	175 ⁽¹⁾	ps (p-p)
t _{OUTPJ_DC} (5)	Period Jitter for dedicated clock output (f _{OUT} < 100 MHz)	_	_	17.5 ⁽¹⁾	mUI (p-p)
+ (5)	Period Jitter for dedicated clock output in fractional PLL ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	250 ⁽¹¹⁾ , 175 ⁽¹²⁾	ps (p-p)
t _{FOUTPJ_DC} (5)	Period Jitter for dedicated clock output in fractional PLL (f _{OUT} < 100 MHz)	_	_	25 ⁽¹¹⁾ , 17.5 ⁽¹²⁾	mUI (p-p)
+ (5)	Cycle-to-Cycle Jitter for a dedicated clock output $(f_{OUT} \ge 100 \text{ MHz})$	_	_	175	ps (p-p)
t _{outccj_dc} (5)	Cycle-to-Cycle Jitter for a dedicated clock output (f _{OUT} < 100 MHz)	_	_	17.5	mUI (p-p)
+ (5)	Cycle-to-cycle Jitter for a dedicated clock output in fractional PLL ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	250 ⁽¹¹⁾ , 175 ⁽¹²⁾	ps (p-p)
t _{FOUTCCJ_DC} ⁽⁵⁾	Cycle-to-cycle Jitter for a dedicated clock output in fractional PLL (f _{OUT} < 100 MHz)+	_	_	25 ⁽¹¹⁾ , 17.5 ⁽¹²⁾	mUI (p-p)
t _{OUTPJ_IO} (5),	Period Jitter for a clock output on a regular I/O in integer PLL ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	600	ps (p-p)
(8)	Period Jitter for a clock output on a regular I/O (f _{OUT} < 100 MHz)	_	_	60	mUI (p-p)
t _{FOUTPJ 10} (5),	Period Jitter for a clock output on a regular I/O in fractional PLL ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	600 (10)	ps (p-p)
(8), (11)	Period Jitter for a clock output on a regular I/O in fractional PLL (f_{OUT} < 100 MHz)	_	_	60 (10)	mUI (p-p)
t _{outccj_10} (5),	Cycle-to-cycle Jitter for a clock output on a regular I/O in integer PLL ($f_{OUT} \ge 100$ MHz)	_	_	600	ps (p-p)
(8)	Cycle-to-cycle Jitter for a clock output on a regular I/O in integer PLL (f_{OUT} < 100 MHz)	_	_	60 (10)	mUI (p-p)
t _{ғоитссу_10}	Cycle-to-cycle Jitter for a clock output on a regular I/O in fractional PLL ($f_{OUT} \ge 100$ MHz)	_	_	600 (10)	ps (p-p)
(8), (11)	Cycle-to-cycle Jitter for a clock output on a regular I/O in fractional PLL (f_{OUT} < 100 MHz)	_	_	60	mUI (p-p)
t _{CASC_OUTPJ_DC}	Period Jitter for a dedicated clock output in cascaded PLLs ($f_{OUT} \ge 100 \text{ MHz}$)	_	_	175	ps (p-p)
(5), (6)	Period Jitter for a dedicated clock output in cascaded PLLs (f _{OUT} < 100 MHz)	_	_	17.5	mUI (p-p)
f _{DRIFT}	Frequency drift after PFDENA is disabled for a duration of 100 μs	_	_	±10	%
dK _{BIT}	Bit number of Delta Sigma Modulator (DSM)	8	24	32	Bits
k _{VALUE}	Numerator of Fraction	128	8388608	2147483648	_

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Table 32. Block Performance Specifications for Stratix V DSP Devices (Part 2 of 2)

		Peformance										
Mode	C1	C2, C2L	12, 12L	C3	13, 13L, 13YY	C4	14	Unit				
		Modes us	ing Three	DSPs	•							
One complex 18 x 25	425	425	415	340	340	275	265	MHz				
	Modes using Four DSPs											
One complex 27 x 27	465	465	465	380	380	300	290	MHz				

Memory Block Specifications

Table 33 lists the Stratix V memory block specifications.

Table 33. Memory Block Performance Specifications for Stratix V Devices (1), (2) (Part 1 of 2)

		Resour	ces Used	Performance								
Memory	Mode	ALUTS	Memory	C1	C2, C2L	C3	C4	12, I2L	13, 13L, 13YY	14	Unit	
	Single port, all supported widths	0	1	450	450	400	315	450	400	315	MHz	
MLAB	Simple dual-port, x32/x64 depth	0	1	450	450	400	315	450	400	315	MHz	
IVILAD	Simple dual-port, x16 depth (3)	0	1	675	675	533	400	675	533	400	MHz	
	ROM, all supported widths	0	1	600	600	500	450	600	500	450	MHz	

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Table 33. Memory Block Performance Specifications for Stratix V Devices (1), (2) (Part 2 of 2)

		Resour	ces Used			Pe	erforman	ce			
Memory	Mode	ALUTS	Memory	C1	C2, C2L	C3	C4	12, 12L	13, 13L, 13YY	14	Unit
	Single-port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	Simple dual-port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	Simple dual-port with the read-during-write option set to Old Data , all supported widths	0	1	525	525	455	400	525	455	400	MHz
M20K Block	Simple dual-port with ECC enabled, 512 × 32	0	1	450	450	400	350	450	400	350	MHz
	Simple dual-port with ECC and optional pipeline registers enabled, 512 × 32	0	1	600	600	500	450	600	500	450	MHz
	True dual port, all supported widths	0	1	700	700	650	550	700	500	450	MHz
	ROM, all supported widths	0	1	700	700	650	550	700	500	450	MHz

Notes to Table 33:

Temperature Sensing Diode Specifications

Table 34 lists the internal TSD specification.

Table 34. Internal Temperature Sensing Diode Specification

Tei	mperature Range	Accuracy	Offset Calibrated Option	Sampling Rate	Conversion Time	Resolution	Minimum Resolution with no Missing Codes
-40°	°C to 100°C	±8°C	No	1 MHz, 500 KHz	< 100 ms	8 bits	8 bits

Table 35 lists the specifications for the Stratix V external temperature sensing diode.

Table 35. External Temperature Sensing Diode Specifications for Stratix V Devices

Description	Min	Тур	Max	Unit
I _{bias} , diode source current	8	_	200	μΑ
V _{bias,} voltage across diode	0.3	_	0.9	V
Series resistance	_	_	<1	Ω
Diode ideality factor	1.006	1.008	1.010	_

⁽¹⁾ To achieve the maximum memory block performance, use a memory block clock that comes through global clock routing from an on-chip PLL set to **50**% output duty cycle. Use the Quartus II software to report timing for this and other memory block clocking schemes.

⁽²⁾ When you use the error detection cyclical redundancy check (CRC) feature, there is no degradation in F_{MAX}.

⁽³⁾ The F_{MAX} specification is only achievable with Fitter options, **MLAB Implementation In 16-Bit Deep Mode** enabled.

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Periphery Performance

This section describes periphery performance, including high-speed I/O and external memory interface.

I/O performance supports several system interfaces, such as the **LVDS** high-speed I/O interface, external memory interface, and the **PCI/PCI-X** bus interface. General-purpose I/O standards such as 3.3-, 2.5-, 1.8-, and 1.5-**LVTTL/LVCMOS** are capable of a typical 167 MHz and 1.2-**LVCMOS** at 100 MHz interfacing frequency with a 10 pF load.



The actual achievable frequency depends on design- and system-specific factors. Ensure proper timing closure in your design and perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specification

Table 36 lists high-speed I/O timing for Stratix V devices.

Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 1 of 4)

<u> </u>				· · · · · · · · · · · · · · · · · · ·										
Cumbal	Conditions		C1		C2,	C2L, I	2, I2L	C3,	13, I3L	., I3YY		C4,I	4	Unit
Symbol	Conuntions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Ullit
f _{HSCLK_in} (input clock frequency) True Differential I/O Standards	Clock boost factor W = 1 to 40 (4)	5		800	5	_	800	5		625	5		525	MHz
f _{HSCLK_in} (input clock frequency) Single Ended I/O Standards ⁽³⁾	Clock boost factor W = 1 to 40 (4)	5		800	5	_	800	5		625	5		525	MHz
f _{HSCLK_in} (input clock frequency) Single Ended I/O Standards	Clock boost factor W = 1 to 40 (4)	5		520	5	_	520	5		420	5		420	MHz
f _{HSCLK_OUT} (output clock frequency)	_	5		800	5	_	800	5		625 (5)	5		525 (5)	MHz

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Table 36. High-Speed I/O Specifications for Stratix V Devices (1), (2) (Part 3 of 4)

			C1		C2,	C2L, I	2, I2L	C3,	13, I3L	., I3YY		C4,I4	4	
Symbol	Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
t _{DUTY}	Transmitter output clock duty cycle for both True and Emulated Differential I/O Standards	45	50	55	45	50	55	45	50	55	45	50	55	%
	True Differential I/O Standards	_	_	160	_	_	160	_	_	200	_	_	200	ps
t _{RISE} & t _{FALL}	Emulated Differential I/O Standards with three external output resistor networks	_		250	_	_	250	_		250	_		300	ps
	True Differential I/O Standards	_	_	150	_		150		_	150		_	150	ps
TCCS	Emulated Differential I/O Standards	_	_	300	_	_	300	_		300	_		300	ps
Receiver														
	SERDES factor J = 3 to 10 (11), (12), (13), (14), (15), (16)	150	_	1434	150	_	1434	150	_	1250	150	_	1050	Mbps
True Differential I/O Standards	SERDES factor J ≥ 4 LVDS RX with DPA (12), (14), (15), (16)	150	_	1600	150	_	1600	150	_	1600	150	_	1250	Mbps
- f _{HSDRDPA} (data rate)	SERDES factor J = 2, uses DDR Registers	(6)	_	(7)	(6)	_	(7)	(6)		(7)	(6)		(7)	Mbps
	SERDES factor J = 1, uses SDR Register	(6)	_	(7)	(6)	_	(7)	(6)		(7)	(6)	_	(7)	Mbps

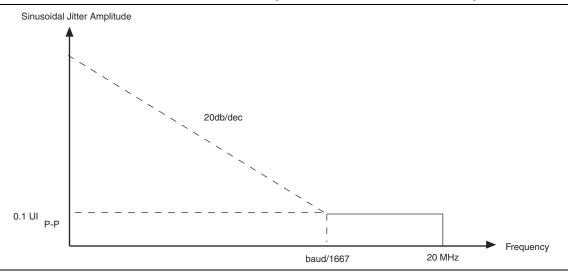
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Table 38. LVDS Soft-CDR/DPA Sinusoidal Jitter Mask Values for a Data Rate \geq 1.25 Gbps

Jitter F	requency (Hz)	Sinusoidal Jitter (UI)
F1	10,000	25.000
F2	17,565	25.000
F3	1,493,000	0.350
F4	50,000,000	0.350

Figure 9 shows the **LVDS** soft-CDR/DPA sinusoidal jitter tolerance specification for a data rate < 1.25 Gbps.

Figure 9. LVDS Soft-CDR/DPA Sinusoidal Jitter Tolerance Specification for a Data Rate < 1.25 Gbps



DLL Range, DQS Logic Block, and Memory Output Clock Jitter Specifications

Table 39 lists the DLL range specification for Stratix V devices. The DLL is always in 8-tap mode in Stratix V devices.

Table 39. DLL Range Specifications for Stratix V Devices (1)

C1	C2, C2L, I2, I2L	C3, I3, I3L, I3YY	C4,I4	Unit
300-933	300-933	300-890	300-890	MHz

Note to Table 39:

(1) Stratix V devices support memory interface frequencies lower than 300 MHz, although the reference clock that feeds the DLL must be at least 300 MHz. To support interfaces below 300 MHz, multiply the reference clock feeding the DLL to ensure the frequency is within the supported range of the DLL.

Table 40 lists the DQS phase offset delay per stage for Stratix V devices.

Table 40. DQS Phase Offset Delay Per Setting for Stratix V Devices (1), (2) (Part 1 of 2)

Speed Grade	Min	Max	Unit
C1	8	14	ps
C2, C2L, I2, I2L	8	14	ps
C3,I3, I3L, I3YY	8	15	ps

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Table 49. DCLK-to-DATA[] Ratio (1) (Part 2 of 2)

Configuration Scheme	Decompression	Design Security	DCLK-to-DATA[] Ratio
FPP ×32	Disabled	Disabled	1
	Disabled	Enabled	4
	Enabled	Disabled	8
	Enabled	Enabled	8

Note to Table 49:

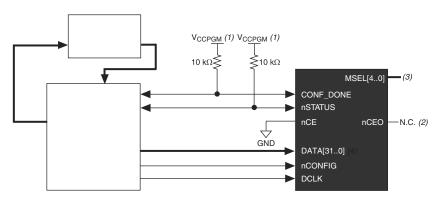
(1) Depending on the DCLK-to-DATA [] ratio, the host must send a DCLK frequency that is r times the data rate in bytes per second (Bps), or words per second (Wps). For example, in FPP ×16 when the DCLK-to-DATA [] ratio is 2, the DCLK frequency must be 2 times the data rate in Wps. Stratix V devices use the additional clock cycles to decrypt and decompress the configuration data.



If the DCLK-to-DATA[] ratio is greater than 1, at the end of configuration, you can only stop the DCLK (DCLK-to-DATA[] ratio -1) clock cycles after the last data is latched into the Stratix V device.

Figure 11 shows the configuration interface connections between the Stratix V device and a MAX II or MAX V device for single device configuration.

Figure 11. Single Device FPP Configuration Using an External Host



Notes to Figure 11:

- (1) Connect the resistor to a supply that provides an acceptable input signal for the Stratix V device. V_{CCPGM} must be high enough to meet the V_{IH} specification of the I/O on the device and the external host. Altera recommends powering up all configuration system I/Os with V_{CCPGM}.
- (2) You can leave the nceo pin unconnected or use it as a user I/O pin when it does not feed another device's nce pin.
- (3) The MSEL pin settings vary for different data width, configuration voltage standards, and POR delay. To connect MSEL, refer to the MSEL Pin Settings section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.
- (4) If you use FPP $\times 8$, use DATA [7..0]. If you use FPP $\times 16$, use DATA [15..0].

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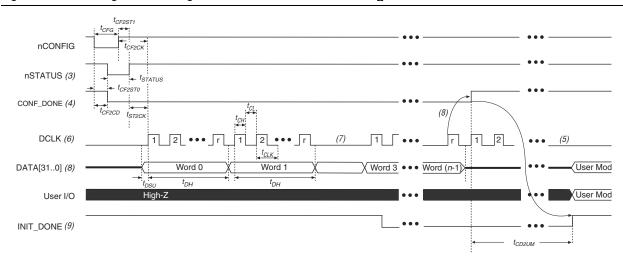


Figure 13. FPP Configuration Timing Waveform When the DCLK-to-DATA[] Ratio is >1 (1), (2)

Notes to Figure 13:

- (1) Use this timing waveform and parameters when the DCLK-to-DATA [] ratio is >1. To find out the DCLK-to-DATA [] ratio for your system, refer to Table 49 on page 55.
- (2) The beginning of this waveform shows the device in user mode. In user mode, nconfig, nstatus, and conf_done are at logic high levels. When nconfig is pulled low, a reconfiguration cycle begins.
- (3) After power-up, the Stratix V device holds nSTATUS low for the time as specified by the POR delay.
- (4) After power-up, before and during configuration, CONF DONE is low.
- (5) Do not leave DCLK floating after configuration. You can drive it high or low, whichever is more convenient.
- (6) "r" denotes the DCLK-to-DATA[] ratio. For the DCLK-to-DATA[] ratio based on the decompression and the design security feature enable settings, refer to Table 49 on page 55.
- (7) If needed, pause DCLK by holding it low. When DCLK restarts, the external host must provide data on the DATA [31..0] pins prior to sending the first DCLK rising edge.
- (8) To ensure a successful configuration, send the entire configuration data to the Stratix V device. CONF_DONE is released high after the Stratix V device receives all the configuration data successfully. After CONF_DONE goes high, send two additional falling edges on DCLK to begin initialization and enter user mode.
- (9) After the option bit to enable the INIT DONE pin is configured into the device, the INIT DONE goes low.

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Table 51 lists the timing parameters for Stratix V devices for FPP configuration when the DCLK-to-DATA [] ratio is more than 1.

Table 51. FPP Timing Parameters for Stratix V Devices When the DCLK-to-DATA[] Ratio is >1 $^{(1)}$

Symbol	Parameter	Minimum	Maximum	Units
t _{CF2CD}	nconfig low to conf_done low	_	600	ns
t _{CF2ST0}	nconfig low to nstatus low	_	600	ns
t _{CFG}	nCONFIG low pulse width	2	_	μS
t _{STATUS}	nstatus low pulse width	268	1,506 ⁽²⁾	μS
t _{CF2ST1}	nconfig high to nstatus high	_	1,506 ⁽²⁾	μS
t _{CF2CK} (5)	nconfig high to first rising edge on DCLK	1,506	_	μS
t _{ST2CK} (5)	nstatus high to first rising edge of DCLK	2	_	μS
t _{DSU}	DATA[] setup time before rising edge on DCLK	5.5	_	ns
t _{DH}	DATA[] hold time after rising edge on DCLK	N-1/f _{DCLK} ⁽⁵⁾	_	S
t _{CH}	DCLK high time	$0.45 \times 1/f_{MAX}$	_	S
t _{CL}	DCLK low time	$0.45 \times 1/f_{MAX}$	_	S
t _{CLK}	DCLK period	1/f _{MAX}	_	S
f	DCLK frequency (FPP ×8/×16)	_	125	MHz
f _{MAX}	DCLK frequency (FPP ×32)	_	100	MHz
t _R	Input rise time	_	40	ns
t _F	Input fall time	_	40	ns
t _{CD2UM}	CONF_DONE high to user mode (3)	175	437	μS
t _{CD2CU}	CONF_DONE high to CLKUSR enabled	4 × maximum DCLK period	_	_
t _{CD2UMC}	CONF_DONE high to user mode with CLKUSR option on	t _{CD2CU} + (8576 × CLKUSR period) ⁽⁴⁾	_	_

Notes to Table 51:

- (1) Use these timing parameters when you use the decompression and design security features.
- (2) You can obtain this value if you do not delay configuration by extending the nconfig or nstatus low pulse width.
- (3) The minimum and maximum numbers apply only if you use the internal oscillator as the clock source for initializing the device.
- (4) To enable the CLKUSR pin as the initialization clock source and to obtain the maximum frequency specification on these pins, refer to the Initialization section of the "Configuration, Design Security, and Remote System Upgrades in Stratix V Devices" chapter.
- (5) N is the DCLK-to-DATA ratio and f_{DCLK} is the DCLK frequency the system is operating.
- (6) If nSTATUS is monitored, follow the t_{ST2CK} specification. If nSTATUS is not monitored, follow the t_{CF2CK} specification.

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Table 58. IOE Programmable Delay for Stratix V Devices (Part 2 of 2)

Parameter	Parameter Available Min	Min	Fast	Model	Slow Model							
(1)	Settings	Offset (2)	Industrial	Commercial	C1	C2	C3	C4	12	13, 13YY	14	Unit
D3	8	0	1.587	1.699	2.793	2.793	2.992	3.192	2.811	3.047	3.257	ns
D4	64	0	0.464	0.492	0.838	0.838	0.924	1.011	0.843	0.920	1.006	ns
D5	64	0	0.464	0.493	0.838	0.838	0.924	1.011	0.844	0.921	1.006	ns
D6	32	0	0.229	0.244	0.415	0.415	0.458	0.503	0.418	0.456	0.499	ns

Notes to Table 58:

- (1) You can set this value in the Quartus II software by selecting D1, D2, D3, D5, and D6 in the Assignment Name column of Assignment Editor.
- (2) Minimum offset does not include the intrinsic delay.

Programmable Output Buffer Delay

Table 59 lists the delay chain settings that control the rising and falling edge delays of the output buffer. The default delay is 0 ps.

Table 59. Programmable Output Buffer Delay for Stratix V Devices (1)

Symbol	Parameter	Typical	Unit
		0 (default) ps	
D	Rising and/or falling edge	25	ps
D _{OUTBUF}	delay	50	ps
		75	ps

Note to Table 59:

Glossary

Table 60 lists the glossary for this chapter.

Table 60. Glossary (Part 1 of 4)

Letter	Subject	Definitions
Α		
В	_	_
С		
D	_	_
E	_	
	f _{HSCLK}	Left and right PLL input clock frequency.
F	f _{HSDR}	High-speed I/O block—Maximum and minimum LVDS data transfer rate (f _{HSDR} = 1/TUI), non-DPA.
	f _{HSDRDPA}	High-speed I/O block—Maximum and minimum LVDS data transfer rate (f _{HSDRDPA} = 1/TUI), DPA.

⁽¹⁾ You can set the programmable output buffer delay in the Quartus II software by setting the Output Buffer Delay Control assignment to either positive, negative, or both edges, with the specific values stated here (in ps) for the Output Buffer Delay assignment.

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Table 60. Glossary (Part 2 of 4)

Letter	Subject	Definitions
G		
Н	_	_
1		
J	JTAG Timing Specifications	High-speed I/O block—Deserialization factor (width of parallel data bus). JTAG Timing Specifications: TMS TDI TCK TJPZX TDO TJPZX TDO TJPZX TDO TJPZX TDO TJPZX TDO TJPZX TJPZX TDO TJPZX TJPZX TDO TJPZX TJPZX TDO
K L M N	_	
P	PLL Specifications	Diagram of PLL Specifications (1) Switchover CLKOUT Pins Four Core Clock Reconfigurable in User Mode External Feedback Note: (1) Core Clock can only be fed by dedicated clock input pins or PLL outputs.
Q	_	<u> </u>
R	R _L	Receiver differential input discrete resistor (external to the Stratix V device).
	L	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1

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Table 60. Glossary (Part 3 of 4)

Letter	Subject	Definitions					
	SW (sampling window)	Timing Diagram—the period of time during which the data must be valid in order to capture it correctly. The setup and hold times determine the ideal strobe position within the sampling window, as shown: Bit Time 0.5 x TCCS RSKM Sampling Window (SW) 0.5 x TCCS					
S	Single-ended voltage referenced I/O standard	The JEDEC standard for SSTL and HSTL I/O defines both the AC and DC input signal values. The AC values indicate the voltage levels at which the receiver must meet its timing specifications. The DC values indicate the voltage levels at which the final logic state of the receiver is unambiguously defined. After the receiver input has crossed the AC value, the receiver changes to the new logic state. The new logic state is then maintained as long as the input stays beyond the DC threshold. This approach is intended to provide predictable receiver timing in the presence of input waveform ringing: Single-Ended Voltage Referenced I/O Standard VIHACO VIHACO VILLOCO V					
	t _C	High-speed receiver and transmitter input and output clock period.					
	TCCS (channel- to-channel-skew)	The timing difference between the fastest and slowest output edges, including $t_{\rm CO}$ variation and clock skew, across channels driven by the same PLL. The clock is included in the TCCS measurement (refer to the <i>Timing Diagram</i> figure under SW in this table).					
		High-speed I/O block—Duty cycle on the high-speed transmitter output clock.					
T	t _{DUTY}	Timing Unit Interval (TUI) The timing budget allowed for skew, propagation delays, and the data sampling window. (TUI = $1/(\text{receiver input clock frequency multiplication factor}) = t_c/w)$					
	t _{FALL}	Signal high-to-low transition time (80-20%)					
	t _{INCCJ}	Cycle-to-cycle jitter tolerance on the PLL clock input.					
	t _{OUTPJ_IO}	Period jitter on the general purpose I/O driven by a PLL.					
	t _{OUTPJ_DC}	Period jitter on the dedicated clock output driven by a PLL.					
	t _{RISE}	Signal low-to-high transition time (20-80%)					
U	_	_					

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Table 60. Glossary (Part 4 of 4)

Letter	Subject	Definitions
	V _{CM(DC)}	DC common mode input voltage.
	V _{ICM}	Input common mode voltage—The common mode of the differential signal at the receiver.
	V _{ID}	Input differential voltage swing—The difference in voltage between the positive and complementary conductors of a differential transmission at the receiver.
	V _{DIF(AC)}	AC differential input voltage—Minimum AC input differential voltage required for switching.
	V _{DIF(DC)}	DC differential input voltage— Minimum DC input differential voltage required for switching.
	V _{IH}	Voltage input high—The minimum positive voltage applied to the input which is accepted by the device as a logic high.
	V _{IH(AC)}	High-level AC input voltage
	V _{IH(DC)}	High-level DC input voltage
V	V _{IL}	Voltage input low—The maximum positive voltage applied to the input which is accepted by the device as a logic low.
	V _{IL(AC)}	Low-level AC input voltage
	V _{IL(DC)}	Low-level DC input voltage
	V _{OCM}	Output common mode voltage—The common mode of the differential signal at the transmitter.
	V _{OD}	Output differential voltage swing—The difference in voltage between the positive and complementary conductors of a differential transmission at the transmitter.
	V _{SWING}	Differential input voltage
	V _X	Input differential cross point voltage
	V _{OX}	Output differential cross point voltage
W	W	High-speed I/O block—clock boost factor
Х		
Υ		_
Z		